

BYC8X-600

Rectifier diode ultrafast, low switching loss

Rev. 01.mm — 4 April 2006

Preliminary data sheet

1. Product profile

1.1 General description

Ultrafast, epitaxial rectifier diode in a SOD113 (2-lead TO220 full pack) plastic package.

1.2 Features

- Extremely fast switching
- Low reverse recovery current
- Low thermal resistance
- Reduces switching loss in associated MOSFET
- Isolated package

1.3 Applications

- Half-bridge / full bridge switched-mode power supplies
- Half-bridge lighting ballasts
- CCM PFC
- Active power factor correction

1.4 Quick reference data

- $V_R \leq 600 \text{ V}$
- $V_F \leq 1.85 \text{ V}$
- $I_F \leq 8 \text{ A}$
- $t_{rr} \leq 19 \text{ ns}$

2. Pinning information

Table 1: Pinning

| Pin | Description | Simplified outline | Symbol |
|-----|-------------|--------------------|--------|
| 1 | cathode | | |
| 2 | anode | | |
| mb | isolated | | |

3. Ordering information

Table 2: Ordering information

| Type number | Package | | Version |
|-------------|---------|--|---------|
| | Name | Description | |
| BYC8X-600 | TO220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO220 full pack | SOD113 |

4. Limiting values

Table 3: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------|--|--|-----|-----|------|------------------|
| V_{RRM} | repetitive peak reverse voltage | | - | - | 600 | V |
| V_{RWM} | crest working reverse voltage | | - | - | 600 | V |
| V_R | continuous reverse voltage | $T_h \leq 100\text{ }^\circ\text{C}$ | - | - | 500 | |
| $I_{F(AV)}$ | average rectified output current | square wave; $\delta = 0.5$; with reappplied $V_{RRM(MAX)}$; $T_h \leq 64\text{ }^\circ\text{C}$ | - | - | 8 | A |
| I_{FRM} | repetitive peak forward current | $\delta = 0.5$; with reappplied $V_{RRM(MAX)}$; $T_h \leq 64\text{ }^\circ\text{C}$ | - | - | 16 | A |
| I_{FSM} | non-repetitive peak forward current | $t = 10\text{ ms}$; sinusoidal | - | - | 80 | A |
| | | $t = 8.3\text{ ms}$; sinusoidal | - | - | 88 | A |
| T_{stg} | storage temperature | | -40 | - | +150 | $^\circ\text{C}$ |
| T_j | junction temperature | | - | - | 150 | $^\circ\text{C}$ |
| V_{isol} | r.m.s isolation voltage from both terminals to external heatsink | $f = 50\text{ to }60\text{z}$; sinusoidal waveform; R.H. $\leq 65\%$; $T_h = 25\text{ }^\circ\text{C}$ | - | - | 2500 | V |
| C_{isol} | capacitance from both terminals to external heatsink | $f = 1\text{ MHz}$; $T_h = 25\text{ }^\circ\text{C}$ | - | 10 | - | pF |

5. Thermal characteristics

Table 4: Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------|--|---------------------------|-----|-----|-----|------|
| $R_{th(j-h)}$ | thermal resistance from junction to heatsink | with heatsink compound; | - | - | 4.8 | K/W |
| | | without heatsink compound | - | - | 5.9 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | - | 55 | - | K/W |

6. Static characteristics

Table 5: Static characteristics

$T_j = 25\text{ °C}$ unless otherwise specified.

| Symbol | Parameter | Conditions | | | | Unit |
|--------|-----------------|---|-----|-----|------|---------------|
| | | | Min | Typ | Max | |
| V_F | forward voltage | $I_F = 8\text{ A}; T_j = 150\text{ °C}$ | - | 1.4 | 1.85 | V |
| | | $I_F = 16\text{ A}; T_j = 150\text{ °C}$ | - | 1.7 | 2.3 | V |
| | | $I_F = 8\text{ A}$ | - | 2.0 | 2.9 | V |
| I_R | reverse current | $V_R = 600\text{ V}$ | - | 9 | 150 | μA |
| | | $V_R = 500\text{ V}; T_j = 100\text{ °C}$ | - | 1.1 | 3.0 | mA |

7. Dynamic characteristics

Table 6: Dynamic characteristics

| Symbol | Parameter | Conditions | <td> | | | Unit |
|-----------|-------------------------------|--|------|-----|-----|------|
| | | | Min | Typ | Max | |
| t_{rr} | reverse recovery time | $I_F = 1 \text{ A}$ to $V_R = 30 \text{ V}$; $di_F/dt = 50 \text{ A} / \mu\text{s}$ | - | 30 | 52 | ns |
| t_{rr} | reverse recovery time | $I_F = 8 \text{ A}$ to $V_R = 400 \text{ V}$; $di_F/dt = 500 \text{ A} / \mu\text{s}$ | - | 19 | - | ns |
| t_{rr} | reverse recovery time | $I_F = 8 \text{ A}$ to $V_R = 400 \text{ V}$; $di_F/dt = 500 \text{ A} / \mu\text{s}$; $T_J = 100 \text{ }^\circ\text{C}$ | - | 32 | 40 | ns |
| I_{rrm} | peak reverse recovery current | $I_F = 8 \text{ A}$ to $V_R = 400 \text{ V}$; $di_F/dt = 50 \text{ A} / \mu\text{s}$; $T_J = 125 \text{ }^\circ\text{C}$ | - | 1.5 | 5.5 | A |
| I_{rrm} | peak reverse recovery current | $I_F = 8 \text{ A}$ to $V_R = 400 \text{ V}$; $di_F/dt = 50 \text{ A} / \mu\text{s}$; $T_J = 100 \text{ }^\circ\text{C}$ | - | 9.5 | 12 | A |
| V_{fr} | forward recovery voltage | $I_F = 10 \text{ A}$; $di_F/dt = 100 \text{ A} / \mu\text{s}$ | - | 8 | 10 | V |

8. Revision history

Table 7: Revision history

| Document ID | Release date | Data sheet status | Change notice | Doc. number | Supersedes |
|-------------|--------------|----------------------------------|---------------|-------------|------------|
| BCY8X_600_1 | | Preliminary text only data sheet | - | - | - |

9. Data sheet status

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|-------|----------------------------------|-----------------------------------|--|
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